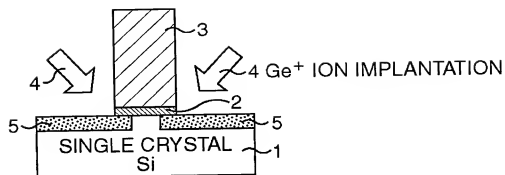


FIG. 1



PARTS UNDER GATE ELECTRODE ALSO AMORPHOUSIZED
BY OBLIQUE AMORPHOUSIZING IMPLANTATION
(IMPURITIES IN THESE PARTS ACTIVATED)

FIG. 2

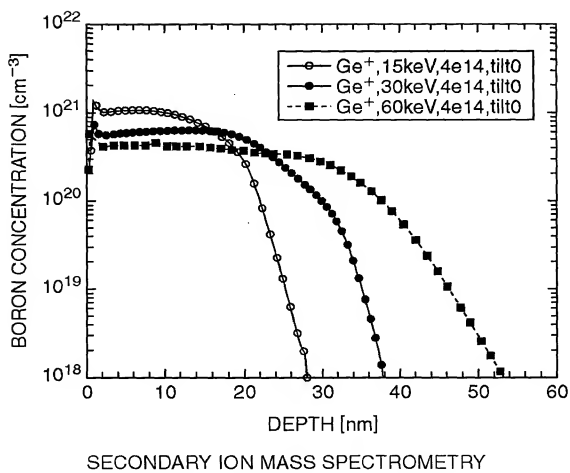
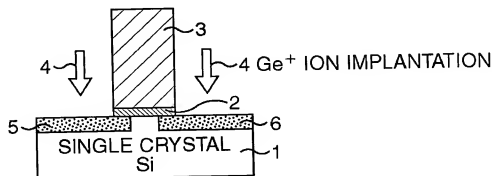


FIG. 3



SOURCE/DRAINS HAVING PARTS UNDER GATE ELECTRODE ALSO AMORPHOUSIZED FORMED BY CONTROLLING ION IMPLANTATION CONDITION AND LASER IRRADIATION CONDITION (IMPURITIES IN THESE PARTS ACTIVATED)

FIG. 4

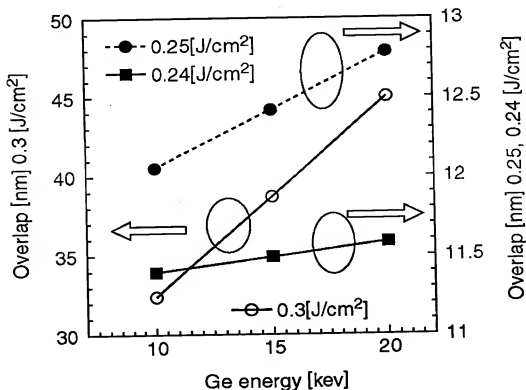


FIG. 5A

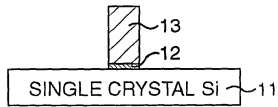


FIG. 5B

A1 Ge⁺ ION IMPLANTATION

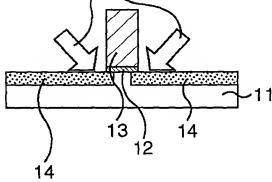


FIG. 5C

A2 B⁺ ION IMPLANTATION

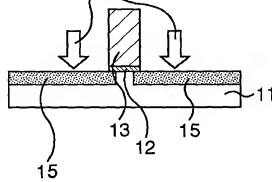


FIG. 5D

A3 Ge⁺ ION IMPLANTATION

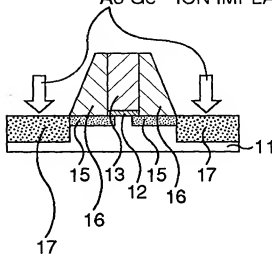


FIG. 5E

A4 B⁺ ION IMPLANTATION

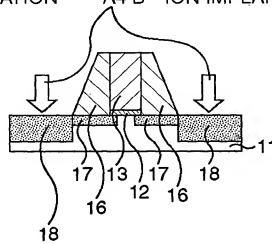


FIG. 6A

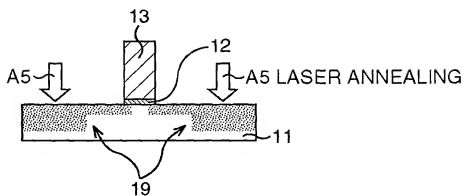


FIG. 6B

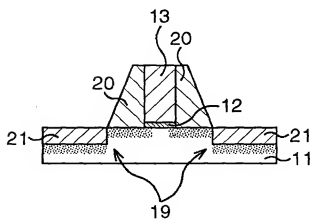


FIG. 6C

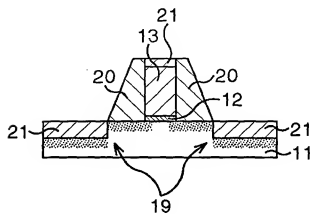


FIG. 7A

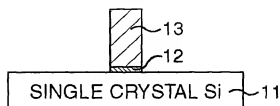


FIG. 7B

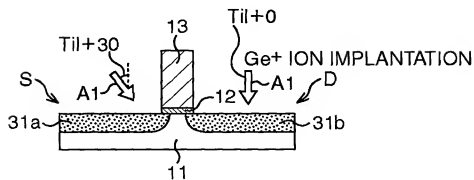


FIG. 7C

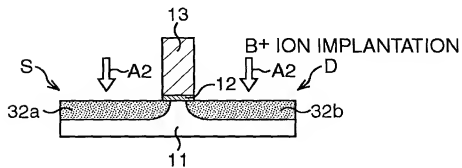


FIG. 7D

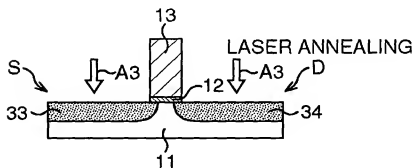


FIG. 8A

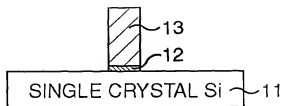


FIG. 8B

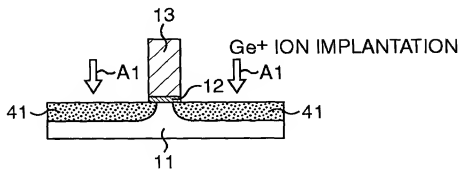


FIG. 8C

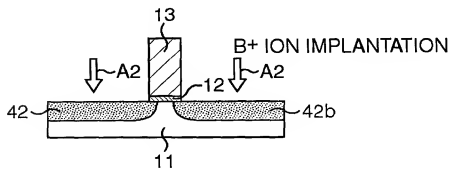
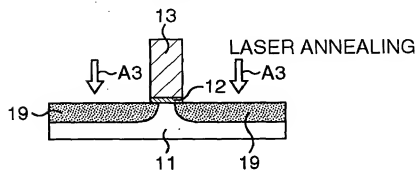


FIG. 8D



202220-4898001

FIG. 9A

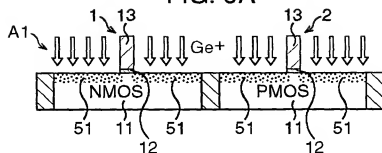


FIG. 9B

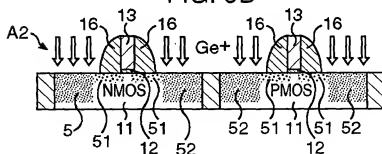


FIG. 9C

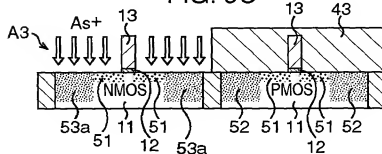


FIG. 9D

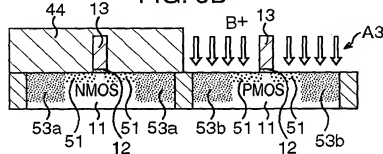


FIG. 9E

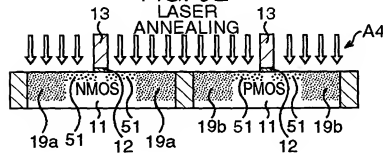


FIG. 10A

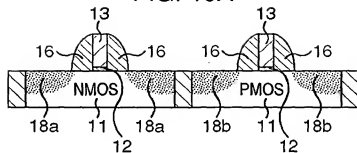


FIG. 10B

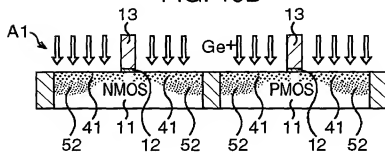


FIG. 10C

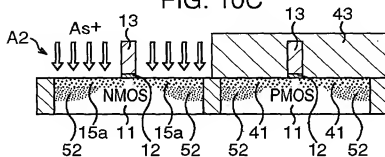


FIG. 10D

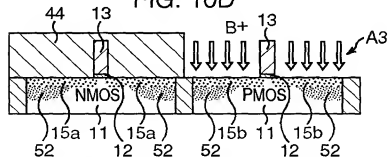


FIG. 10E

